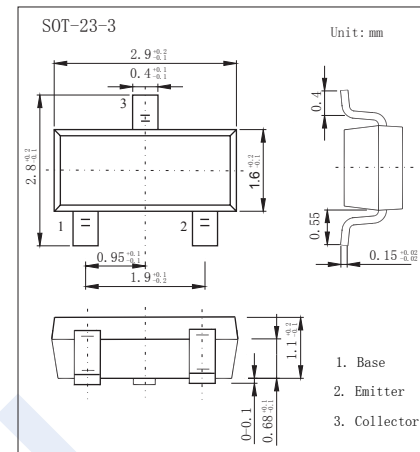


PNP Transistors

2SA1365-HF

■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity of DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.
- Complementary to 2SC3440-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-25	V
Collector - Emitter Voltage	V _{CE0}	-20	
Emitter - Base Voltage	V _{EB0}	-4	
Collector Current - Continuous	I _C	-700	mA
Peak Collector Current	I _{CM}	-1	A
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-25			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -1 mA, I _B =0	-20			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-4			
Collector-base cut-off current	I _{CB0}	V _{CB} = -25 V, I _E =0			-100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = -2V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA, I _B =- 25mA		-0.2	-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-500mA, I _B =- 25mA			-1.2	
DC current gain *	h _{FE}	V _{CE} = -4V, I _C = -100mA	150		800	
Transition frequency	f _T	V _{CE} = -6V, I _E = 10mA	100	180		MHz

* It shows h_{FE} classification in right table.

■ Classification of h_{FE}

Type	2SA1365-E-HF	2SA1365-F-HF	2SA1365-G-HF
Range	150-300	250-500	400-800
Marking	AE _F	AF _F	AG _F

PNP Transistors

2SA1365-HF

■ Typical Characteristics

